

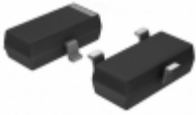






	<p><b>SI2316DS-T1-E3</b></p>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI2316DS-T1-E3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 2.9A SOT23-3</p> <p><b>Datenblätter:</b>  <a href="#">SI2316DS-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 92406 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	<a href="#">SI2316DS-T1-E3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET N-CH 30V 2.9A SOT23-3
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	92406 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	700mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	2.9A (Ta)
Rds On (Max) @ Id, Vgs	50 mOhm @ 3.4A, 10V
VGS (th) (Max) @ Id	800mV @ 250µA (Min)
Gate Charge (Qg) (Max) @ Vgs	7nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	215pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

SI2316DS-T1-E3 ist neu im Original, Suche SI2316DS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2316DS-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2316DS-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI2317DS-T1-E3</b> VISHAY/PL SI2317DS-T1-E3 VISHAY/PL</p>	 <p><b>SI2316BDS-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.5A SOT-23</p>	 <p><b>SI2316DS-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 2.9A SOT23-3</p>	 <p><b>SI2316BDS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.5A SOT23-3</p>
 <p><b>SI2317DS</b> VISAHY SI2317DS VISAHY</p>	 <p><b>SI2316BDS-T1-E3</b> Vishay / Siliconix MOSFET N-CH 30V 4.5A SOT-23</p>	 <p><b>SI2316BDS-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 4.5A SOT23-3</p>	 <p><b>SI2316DS</b> 89K SI2316DS 89K</p>

heiße Teile

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|--|--|--|---|--|
|  SI2313DS-T1-GE3  |  SI2314DS         |  SI2314DS-T1-E3   |  SI2314DS-T1-GE3  |  SI2314EDS        |
|  SI2314EDS-T1-E3  |  SI2314EDS-T1-E3  |  SI2314EDS-T1-GE3 |  SI2314EDS-T1-GE3 |  SI2315BDS        |
|  SI2315BDS-T1-E3  |  SI2315BDS-T1-E3  |  SI2315BDS-T1-GE3 |  SI2315BDS-T1-GE3 |  SI2315DS         |
|  SI2315DS-T1      |  SI2315DS-T1-E3   |  SI2315DS-T1-GE3  |  SI2316-DS        |  SI2316BDS-T1-E3  |
|  SI2316BDS-T1-E3  |  SI2316BDS-T1-GE3 |  SI2316BDS-T1-GE3 |  SI2316DS         |  SI2316DS-T1-E3   |
|  SI2316DS-T1-GE3  |  SI2316DS-T1-GE3  |  SI2317DS         |  SI2317DS-T1-E3   |  SI2318ADS-T1-GE3 |
|  SI2318BDS-T1-E3  |  SI2318BDS-T1-GE3 |  SI2318CDS-T1-E3  |  SI2318CDS-T1-GE3 |  SI2318CDS-T1-GE3 |
|  SI2318DS         |  SI2318DS-T1-E3   |  SI2318DS-T1-E3   |  SI2318DS-T1-GE3  |  SI2318DS-T1-GE3  |
|  SI2319ADS-T1-GE3 |  SI2319C95TF      |  SI2319CDS-T1-E3  |  SI2319CDS-T1-GE3 |  SI2319CDS-T1-GE3 |
|  SI2319DDS-T1-GE3 |  SI2319DS         |  SI2319DS-T1-E3   |  SI2319DS-T1-E3   |  SI2319DS-T1-GE3  |

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